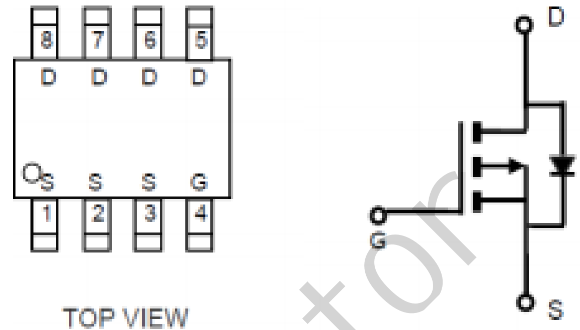
DESCRIPTION

The IRF9388 is the P-Channel logic enhancement mode power field effect transistor is produced using high cell density advanced trench technology..

This high density process is especially tailored to minimize on-state resistance.

This device is suitable for use as a load switch or in PWM and gate charge for most of the synchronous buck converter applications



FEATURE

- ***-30V/-17A, $R_{DS(ON)}$ = 6.8 mΩ (typ.)@V_{GS}=-10V***
- ***-30V/-7.0A, $R_{DS(ON)}$=9.6mΩ (typ.)@V_{GS}=-4.5V***
- Super high design for extremely low $R_{DS(ON)}$
- Exceptional on-resistance and Maximum DC current capability
- Full RoHS compliance
- SOP8 package design

APPLICATIONS

- High Frequency Point-of-Load Synchronous Buck Converter for MB/NB/UMPC/GA
- Newworking DC-DC Power System
- Load Switch
- Power Management in Note Book

JSMICRO Semiconductor

ABSOLUTE MAXIMUM RATINGS *(T_A = 25℃ Unless otherwise noted)*

Symbol	Parameter		Typical	Unit
V_{DSS}	Drain-Source Voltage		-30	V
V_{GSS}	Gate-Source Voltage		±20	V
I_D	Continuous Drain Current (T_A=25℃)	V_{GS}=10V	-17	A
	Continuous Drain Current (T_A=70℃)		-9.5	A
I_{DM}	Pulsed Drain Current		-40	A
I_S	Continuous Source Current (Diode Conduction)		-2.0	A
P_D	Power Dissipation	T_A=25℃	2.0	W
		T_A=70℃	1.5	
T_J	Operation Junction Temperature		150	℃
T_{STG}	Storage Temperature Range		-55~+150	℃
$R_{θJA}$	Thermal Resistance Junction to Ambient		85	℃/W

Note: Absolute maximum ratings are those values beyond which the device could be permanently damaged. Absolute maximum ratings are stress rating only and functional device operation is not implied

■ *ELECTRICAL CHARACTERISTICS(T_A=25℃ Unless otherwise noted)*

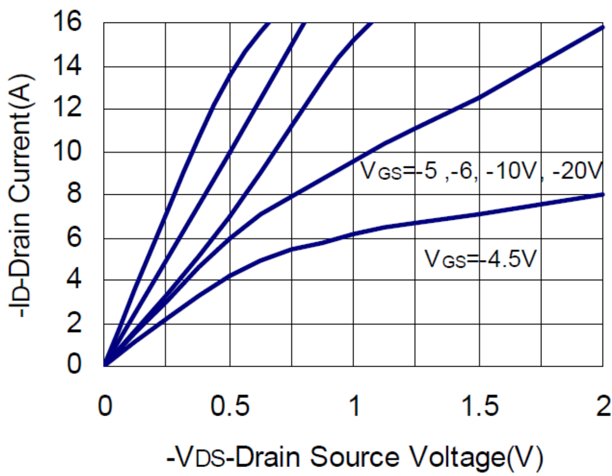
Symbol	Parameter	Condition	Min	Typ	Max	Unit
Static Parameters						
$V_{(BR)DSS}$	Drain-Source Breakdown Voltage	V_{GS}=0V, I_D=-250uA	-30			V
$V_{GS(th)}$	Gate Threshold Voltage	V_{DS}=V_{GS}, I_D=-250uA	-1.0	-1.4	-2.0	V
I_{GSS}	Gate Leakage Current	V_{DS}=0V, V_{GS}=±25V			±100	nA
I_{DSS}	Zero Gate Voltage Drain Current	V_{DS}=-30V, V_{GS}=0			-1	uA
		V_{DS}=-30V, V_{GS}=0 T_J=55℃			-5	
$R_{DS(ON)}$	Drain-Source On-Resistance	V_{GS}=-10V, I_D=-15A		6.8	8	mΩ
		V_{GS}=-4.5V, I_D=-8.0A		9.5	13	
Source-Drain Diode						
V_{SD}	Diode Forward Voltage	I_S=-2.3A, V_{GS}=0V		-0.75	-1.0	V
Dynamic Parameters						
Q_g	Total Gate Charge	V_{DS}=-15V		30	42	nC
Q_{gs}	Gate-Source Charge	V_{GS}=-4.5V		10	14	
Q_{gd}	Gate-Drain Charge	I_D=-10A		10.4	14.6	
C_{iss}	Input Capacitance	V_{DS}=-15V		2050	2730	pF
C_{oss}	Output Capacitance	V_{GS}=0V		506	710	
C_{rss}	Reverse Transfer Capacitance	f=1MHz		420	590	
$T_{d(on)}$	Turn-On Time	V_{DS}=-15V		9.3	19	nS
T_r		I_D=-10A		10.2	18	
$T_{d(off)}$	Turn-Off Time	V_{GEN}=-10V		117	232	
T_f		R_G=3.3Ω		24	46	

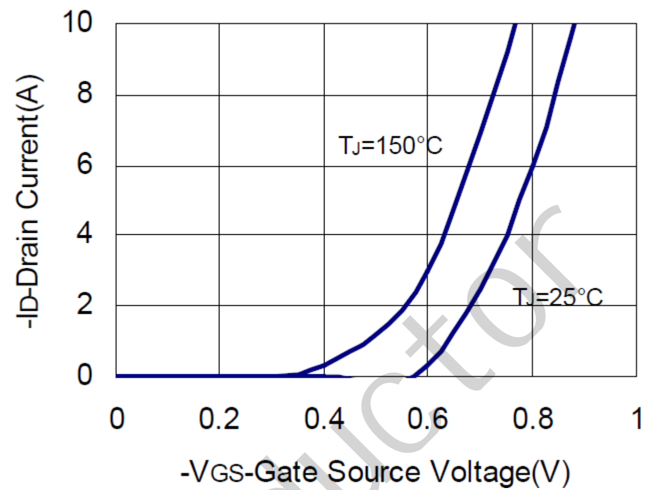
Note: 1. Pulse test: pulse width<=300uS, duty cycle<=2%

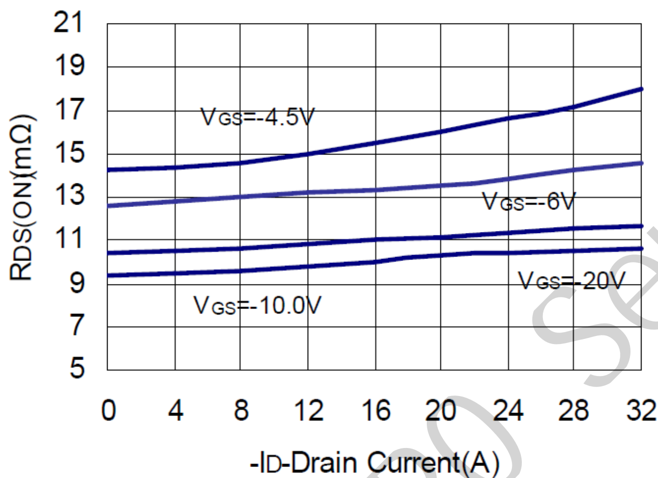
2.Static parameters are based on package level with recommended wire bonding

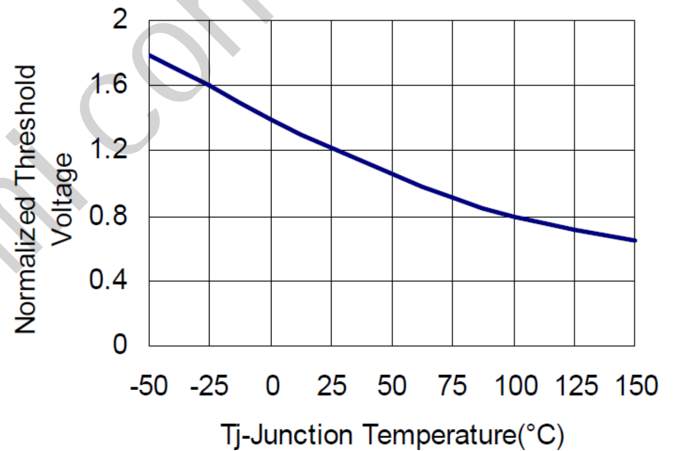
JSMI CRO Semiconductor

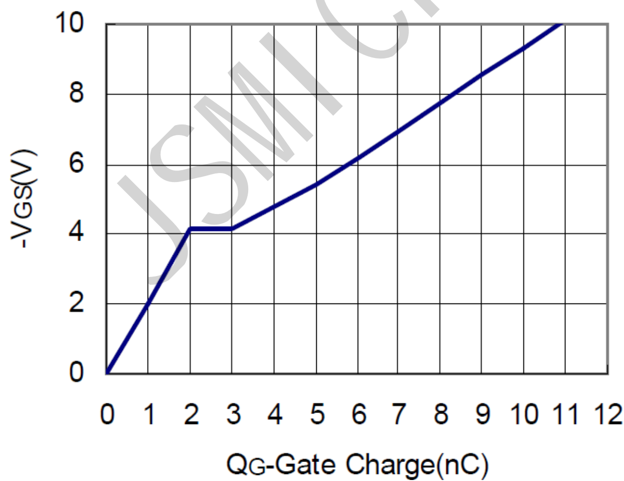
■ *TYPICAL CHARACTERISTICS (25℃ Unless Note)*

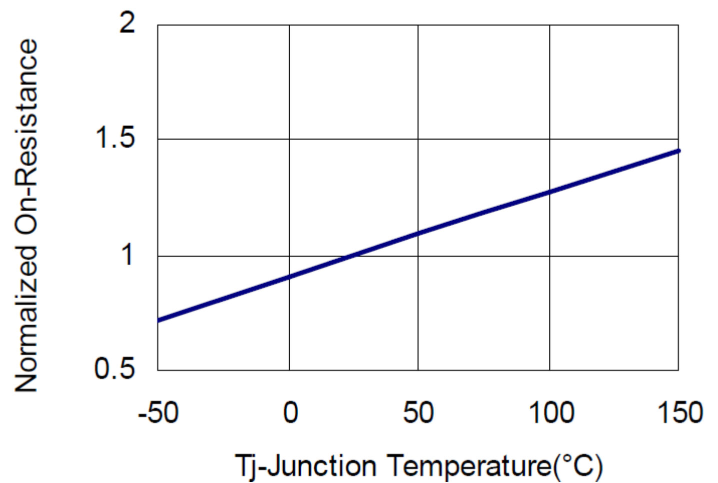






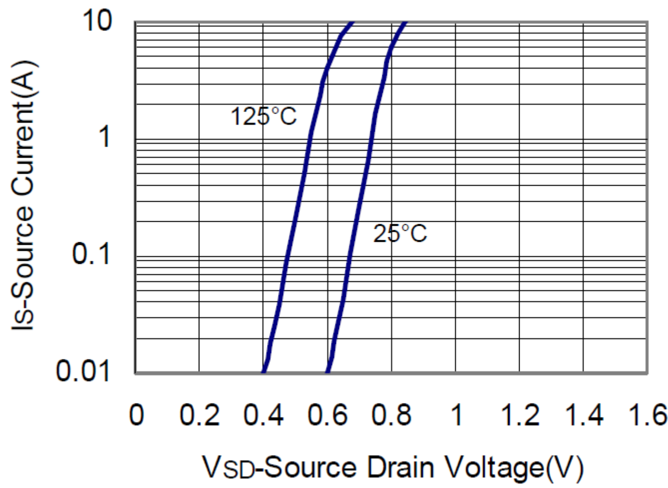


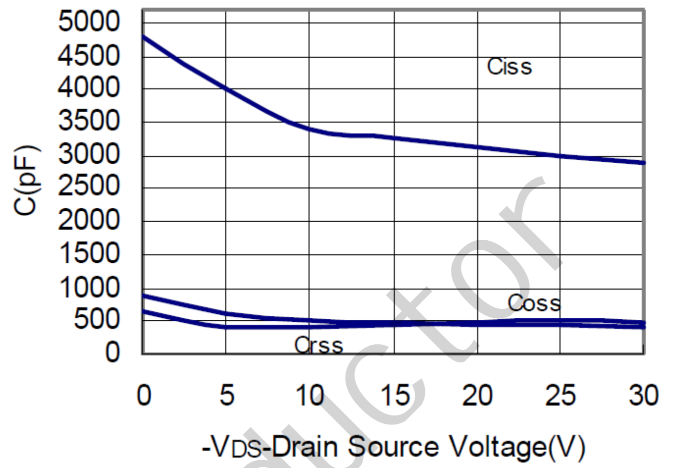


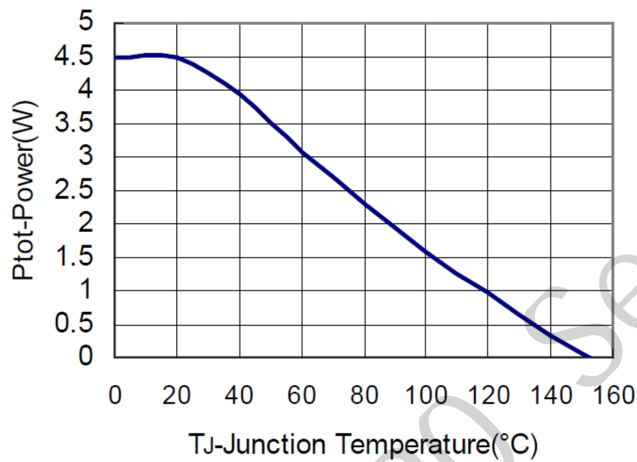


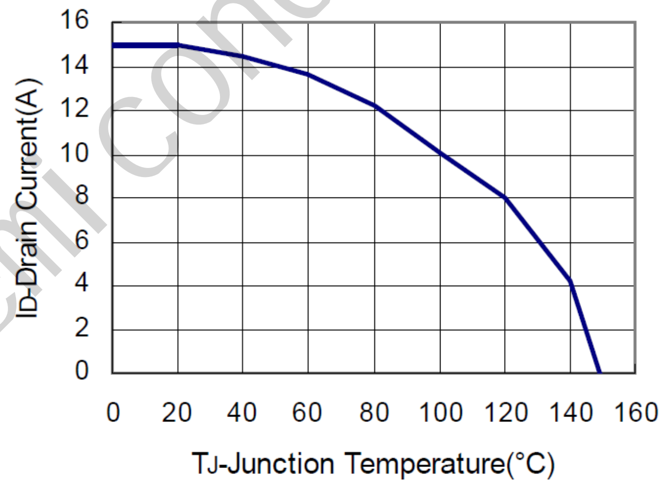
JSMICRO Semiconductor

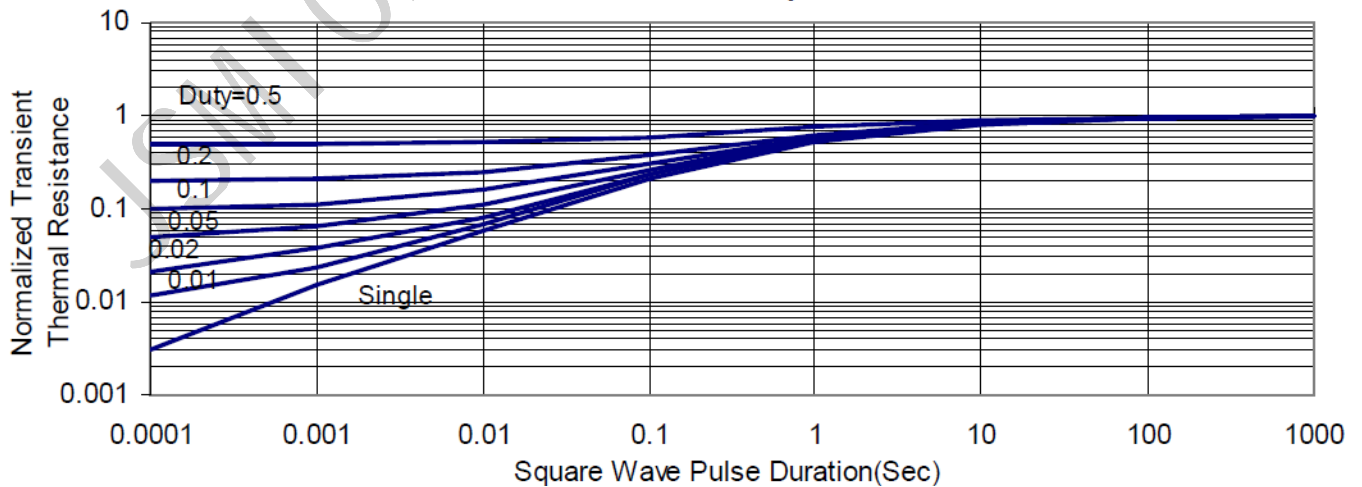
■ *TYPICAL CHARACTERISTICS (continuous)*



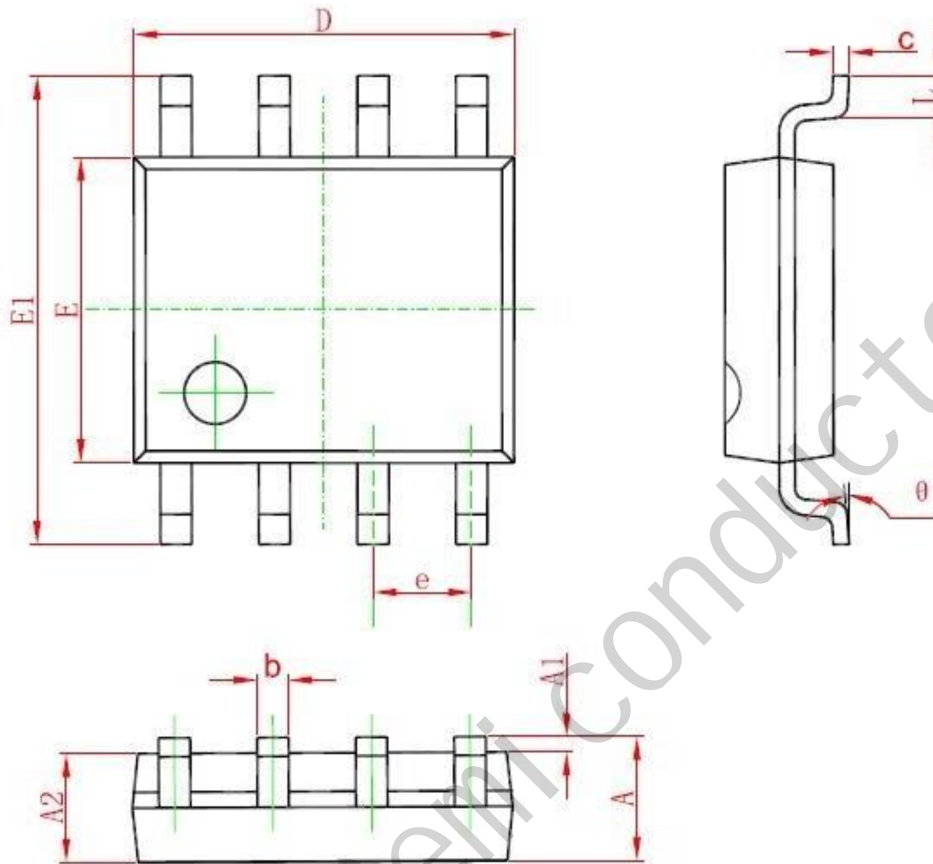








SOP8 PACKAGE OUTLINE DIMENSIONS



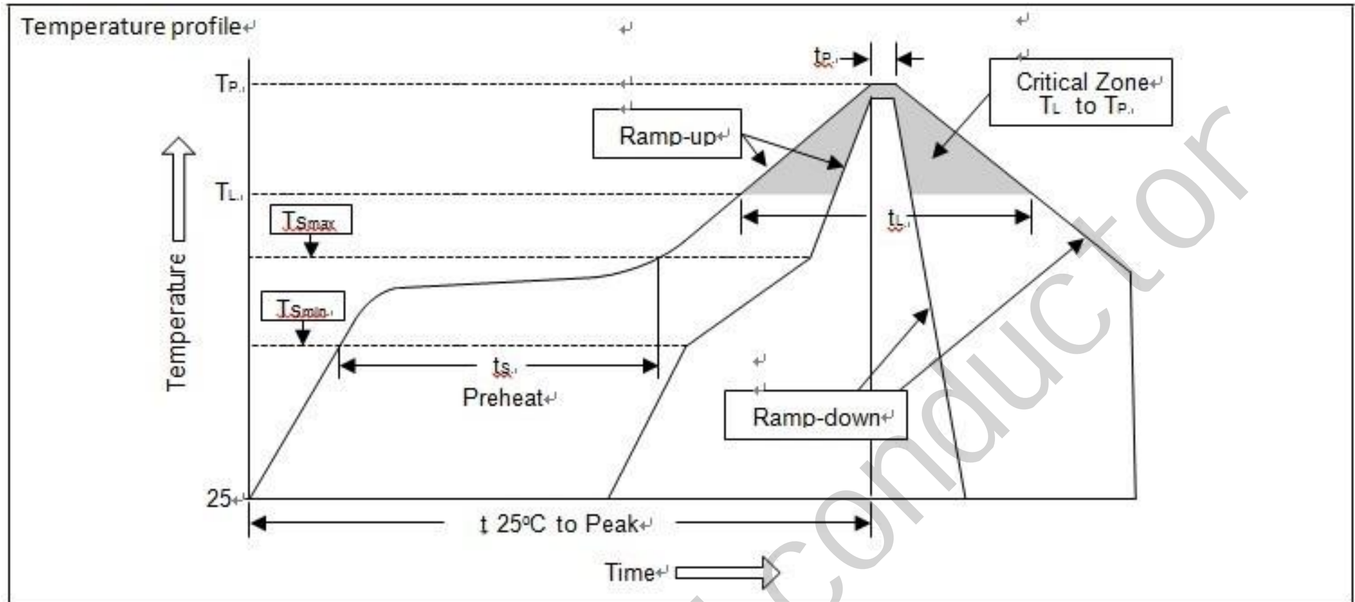
JSMICRO Semiconductor

Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min	Max	Min	Max
A	1.350	1.750	0.053	0.069
A1	0.100	0.250	0.004	0.010
A2	1.350	1.550	0.053	0.061
b	0.330	0.510	0.013	0.020
c	0.170	0.250	0.006	0.010
D	4.700	5.100	0.185	0.200
E	3.800	4.000	0.150	0.157
E1	5.800	6.200	0.228	0.244
e	1.270(BSC)		0.050(BSC)	
L	0.400	1.270	0.016	0.050
θ	0°	8°	0°	8°

■ *SOLDERING METHODS FOR UNIVERCHIP*

Storage environment Temperature=10℃~35℃ Humidity=65%±15%

Reflow soldering of surface mount device



Profile Feature	Sn-Pb Eutectic Assembly	Pb free Assembly
Average ramp-up rate (T_L to T_P)	<3℃/sec	<3℃/sec
Preheat -Temperature Min (Ts_{min}) -Temperature Max (Ts_{max}) -Time (min to max) (ts)	 100℃ 150℃ 60~120 sec	 150℃ 200℃ 60~180 sec
Tsmax to T_L -Ramp-up Rate	<3℃/sec	<3℃/sec
Time maintained above -Temperature (T_L) -Time (t_L)	 183℃ 60~150 sec	 217℃ 60~150 sec
Peak Temperature (T_P)	240℃+0/-5℃	260℃+0/-5℃
Time within 5℃ of actual Peak Temperature (t_P)	10~30 sec	20~40 sec
Ramp-down Rate	<6℃/sec	<6℃/sec
Time 25℃ to Peak Temperature	<6 minutes	<6 minutes

JSMI CRO Semiconductor

Flow (wave) soldering (solder dipping)

Product	Peak Temperature	Dipping Time
Pb device	245℃±5℃	5sec±1sec
Pb-Free device	260℃+0/-5℃	5sec±1sec

This integrated circuit can be damaged by ESD HongChip Corporation recommends that all integrated circuits be handled with appropriate precautions. Failure to observe proper handling and installation procedure can cause damage. ESD damage can range from subtle performance degradation to complete device failure. Precision integrated circuits may be more susceptible to damage because very small parametric changes could cause the device not to meet its published specifications.

JSMICRO Semiconductor